

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A protection circuit for a semiconductor laser device, comprising:

a resistor or coil connected in series with the semiconductor laser device; and

a first capacitor and a second capacitor that are connected in parallel with the semiconductor laser device on opposite sides of the resistor or coil in a  $\Pi$ -type configuration for obtaining high electrostatic breakdown voltage,

wherein said first capacitor has a low impedance in a frequency region and said second capacitor has a low impedance in a frequency region different from the frequency region for the low impedance of the first capacitor, and the electrostatic breakdown voltage is increased.

2. (Original) The protection circuit for a semiconductor laser device according to Claim 1, wherein one of the first and second capacitors is a low frequency capacitor, while the other

of the first and second capacitors is a high frequency capacitor.

3. (*Previously Presented*) The protection circuit for a semiconductor laser device according to Claim 2, wherein the low frequency capacitor is placed less closer to the semiconductor laser device than the high frequency capacitor.

4. (*Original*) The protection circuit for a semiconductor laser device according to Claim 1, wherein both of the first and second capacitors are multilayered ceramic chip capacitors, and the resistor or coil is a chip resistor or chip coil.

5. (*Original*) The protection circuit for a semiconductor laser device according to Claim 1, wherein the first and second capacitors and the resistor or coil are mounted on a circuit board on which the semiconductor laser device is mounted, the second capacitor and the resistor or coil are disposed in the vicinity of a terminal of the semiconductor laser device, and the first capacitor is disposed in the vicinity of an input terminal of the circuit board.

6. (*Original*) The protection circuit for a semiconductor laser device according to Claim 5, wherein the circuit board has a plurality of wiring lines including a wiring line to supply

the semiconductor laser device with an electrical current, and the protection circuit further comprises a metallic pattern for grounding that is formed outside of the plurality of wiring lines and at least along the wiring line to supply the semiconductor laser device with an electrical current.

7. (*Previously Presented*) The protection circuit for a semiconductor laser device according to Claim 5, wherein the first capacitor is a low frequency capacitor, and the second capacitor is a high frequency capacitor.

8. (*Currently Amended*) A protection circuit for a semiconductor laser device, comprising:

a resistor or coil connected in series with the semiconductor laser device; and

a low frequency capacitor and a high frequency capacitor that are connected in parallel with the semiconductor laser device on opposite sides of the resistor or coil in a  $\Pi$ -type configuration for obtaining high electrostatic breakdown voltage.

9. (*Previously Presented*) The protection circuit for a semiconductor laser device according to Claim 8, wherein the low

frequency capacitor is placed less closer to the semiconductor laser device than the high frequency capacitor.

10. (*Previously Presented*) The protection circuit for a semiconductor laser device according to Claim 8, wherein both of the low frequency and high frequency capacitors are multilayered ceramic chip capacitors, and the resistor or coil is a chip resistor or chip coil.

11. (*Original*) The protection circuit for a semiconductor laser device according to Claim 8, wherein the low frequency and high frequency capacitors and the resistor or coil are mounted on a circuit board on which the semiconductor laser device is mounted, the high frequency capacitor and the resistor or coil are disposed in the vicinity of a terminal of the semiconductor laser device, and the low frequency capacitor is disposed in the vicinity of an input terminal of the circuit board.

12. (*Original*) The protection circuit for a semiconductor laser device according to Claim 11, wherein the circuit board has a plurality of wiring lines including a wiring line to supply the semiconductor laser device with an electrical current, and the protection circuit further comprises a metallic pattern for grounding that is formed outside of the plurality of

wiring lines and at least along the wiring line to supply the semiconductor laser device with an electrical current.

13. (*Currently Amended*) A protection circuit for a semiconductor laser device, comprising:

a resistor or coil connected in series with the semiconductor laser device; and

a first capacitor and a second capacitor that are connected in parallel with the semiconductor laser device on opposite sides of the resistor or coil in a  $\Pi$ -type configuration for obtaining high electrostatic breakdown voltage, the first capacitor and/or the second capacitor being a capacitor in which a low frequency capacitor and a high frequency capacitor are connected in parallel for increasing the electrostatic breakdown voltage.

14. (*Original*) The protection circuit for a semiconductor laser device according to Claim 13, wherein both of the first and second capacitors are multilayered ceramic chip capacitors, and the resistor or coil is a chip resistor or chip coil.

15. (*Original*) The protection circuit for a semiconductor laser device according to Claim 13, wherein the first and second capacitors and the resistor or coil are mounted on a circuit

board on which the semiconductor laser device is mounted, the second capacitor and the resistor or coil are disposed in the vicinity of a terminal of the semiconductor laser device, and the first capacitor is disposed in the vicinity of an input terminal of the circuit board.

16. (*Original*) The protection circuit for a semiconductor laser device according to Claim 15, wherein the circuit board has a plurality of wiring lines including a wiring line to supply the semiconductor laser device with an electrical current, and the protection circuit further comprises a metallic pattern for grounding that is formed outside of the plurality of wiring lines and at least along the wiring line to supply the semiconductor laser device with an electrical current.

17. (*Original*) The protection circuit for a semiconductor laser device according to Claim 1, wherein the first and second capacitors have an identical capacitance.

18. (*Original*) The protection circuit for a semiconductor laser device according to Claim 8, wherein the low frequency capacitor has a capacitance of 1  $\mu\text{F}$  and the high frequency capacitor has a capacitance of 0.1  $\mu\text{F}$ .

19. (*Original*) The protection circuit for a semiconductor laser device according to Claim 13, wherein the low frequency capacitor has a capacitance of 1  $\mu$ F and the high frequency capacitor has a capacitance of 0.1  $\mu$ F.

20. (*Previously Presented*) The protection circuit for a semiconductor laser device according to Claim 8, wherein said low frequency capacitor has a low impedance in a low frequency region, and said high frequency capacitor has a low impedance in a high frequency region.

21. (*Previously Presented*) The protection circuit for a semiconductor laser device according to Claim 13, wherein said low frequency capacitor has a low impedance in a low frequency region, and said high frequency capacitor has a low impedance in a high frequency region.